AlGaInP/Si Hyper Red Chip ---TK540UOH

1. Scope

- AlGaInP High- Brightness LED chip.

2. Structure

- AlGaInP on Silicon
- N Electrode (cathode) side : Gold
- P Electrode (anode) side : Gold Alloy

3. Size

- Chip size : 40 mil × 40 mil (1000 um × 1000 um)
- Chip height : 200 ± 10 um
- Pattern drawing : per fig. 1

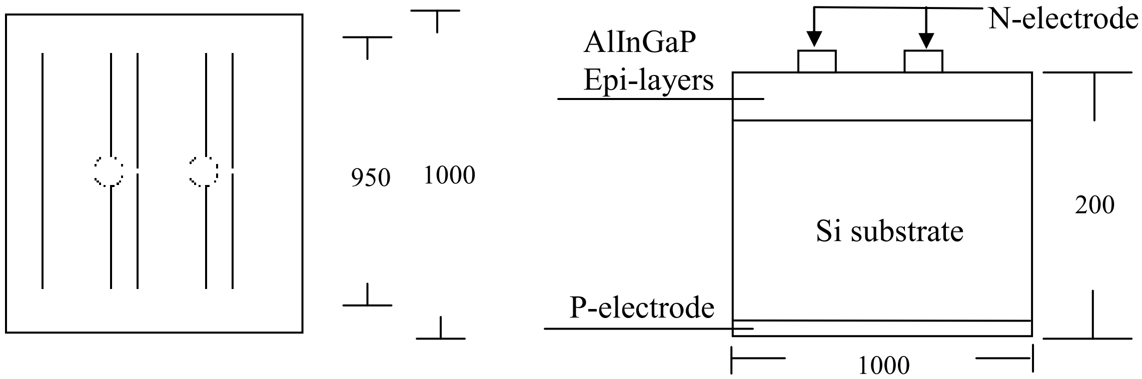
4. Electro-Optical Characteristics

(Ta = +25 ℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	I_F =350 mA		2.5	2.7	V
Reverse Voltage	I_R	I_R = 10 V			10	μA
Luminous Intensity	I_V	I_F =350 mA	※			mcd
Wavelength	λ d	I_F =20 mA	620	625	630	nm
Spectrum Width of Half Value	Δ λ	I_F =20 mA		20		nm

Maximum reverse-biased voltage < 60V; therefore, V_Z test is forbidden.

※ • Rank R : min.≧4300
• Rank S : min.≧5000
• Rank T : min.≧5700



***Recommendation for bonding condition :**

bonding force 40 g, bonding temperature 280℃, bonding time 20 ms.

***Storage condition**： temperature 0 ~ 35℃, humidity≦60% RH.

Unit：μm

fig. 1

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